# **Supporting Information**

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**Fig. S1.** Graphical representation of  $H(I_X)$  in the equation for  $p_{cap}$  (Eq. 2) with  $f(I) = (1 + e^{-1})^{-1}$ 



Fig. S2. Effect of changes in G<sup>+</sup>, G<sup>-</sup>, or *I<sub>X</sub>* on memory capacity and persistent activity. Changes in parameters that lead to improved capacity generally increase network activity. (*Top*) Firing rate of memories at different loads. (*Middle*) Graphical solutions of the capacity equation for two different loads, *p* 1 and 3. As *p* increases, the line representing the effective network synaptic strength shifts leftward. (*Bottom*) Potential energy landscape of the network at loads 1 and 3. Energy minima represent stable states. (A) Reference parameter set used in Fig. 2:  $A = 0.1$ ,  $G^+ = 22$ ,  $G^- = 2$ ,  $I_X = -6.25$ . When load equals capacity (thin line; here, *p*cap 3.57) the synaptic line is tangential to the neuronal-input output curve in the *Middle*. (*Bottom*) The energy minimum corresponding to the memory state disappears at capacity (thin line). (*B*) Increasing capacity from 3 to 4 by increasing *G*- leads to increased persistent activity at the same load (arrows indicate memory activity at load  $p = 3$ ). For comparison, the reference network is shown in gray. (C) Same for  $G^-$ . (D) Same for *I<sub>X</sub>*. Generally, networks that have higher capacity caused by a change in a  $G^+$ ,  $G^-$ , or  $I_X$  also have higher activity at the same load.

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**Fig. S3.** Working memory capacity in a balanced network. (*A*) The network is stable when the line and the curve intersect in three places. For the value of *IX* in the figure, the golden area represents the region of stable memory activity. The size of this area is determined by the ratio between G<sup>+</sup> and *H*(*I<sub>X</sub>*), which determines the right and left border of the area. (*B*) G†/*H*(/<sub>x</sub>) is in turn determined by the spontaneous activity. For spontaneous rates above ≈1.5, G†/*H*(/<sub>x</sub>) < 1.5. (C) Having determined G<sup>+</sup>/H(I<sub>X</sub>), Eqs. 3 and 56 (see [SI Appendix](http://www.pnas.org/cgi/data/0901894106/DCSupplemental/Appendix_PDF)) can now be used to calculate  $p_{\text{cap}}^{\text{UL}}$  for a given level of spontaneous activity. Note that although *p*cap UL in Eqs. **3** and **s6** (see *[SI Appendix](http://www.pnas.org/cgi/data/0901894106/DCSupplemental/Appendix_PDF)*) is a continuous variable, only a discrete number of stimuli can be presented, making capacity an integer number. The following parameters were used. Standard deviation of input current, determining the linearity of the *f-I* curve:  $\sigma$  = 0.001. w: 0.1.

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Clusters identified testing the global null hypothesis of no activation in either M5–C5 or M3–C3 contrasts, with a threshold at  $P = 0.05$ after correcting for multiple comparisons using the false-discovery rate procedure. Only clusters larger than 100 voxels are shown. \*Identification of areas tagged with lower-case letters in the brain illustration of Fig. 4*B*.

†Brodmann area (BA) estimation from Talairach Daemon Client v2.0 (http://ric.uthscsa.edu/resources) and xjView (http://people.hnl.bcm.tmc.edu/cuixu/xjView/). I, II, III, and IV indicate same activation cluster.

## **Table S2. Cell parameters**



*N*, number of cells; *C*m, membrane capacitance; *g*L, leak conductance; *E*L, leak reversal potential; V<sub>res</sub>, reset potential; V<sub>th</sub>, spike threshold potential; <sub>Tref,</sub> refractory period time constant;  $r_X$ , rate of external afferents. For an explanation of these parameters and the equations they govern, see Compte A, Brunel N, Goldman-Rakic PS, Wang XJ (2000) Synaptic mechanisms and network dynamics underlying spatial working memory in a cortical network model. *Cereb Cortex* 10:910 –923.

#### **Table S3. Synaptic parameters**



 $\tau_{\mathsf{s}}$ , decay time constant for  $\mathsf{s}$ , the fraction of open channels;  $\alpha_{\mathsf{s}}$ , saturation constant;  $\tau_{\mathsf{x}_{\ell}}$  rise time constant;  $\mathsf{V}_{\mathsf{rev}_{\ell}}$  reversal potential. For an explanation of these parameters and the equations they govern, see Compte A, Brunel N, Goldman-Rakic PS, Wang XJ (2000) Synaptic mechanisms and network dynamics underlying spatial working memory in a cortical network model. *Cereb Cortex* 10:910 –923.

## **Table S4. Connectivity**



For an explanation of the parameters and the equations they govern, see Compte A, Brunel N, Goldman-Rakic PS, Wang XJ (2000) Synaptic mechanisms and network dynamics underlying spatial working memory in a cortical network model. *Cereb Cortex* 10:910 –923.

\*Connections from I cells are always GABAAR-mediated.

†X, external afferents.

#### **Table S5. Parameters varied in simulations**



For an explanation of these parameters and the equations they govern, see Compte A, Brunel N, Goldman-Rakic PS, Wang XJ (2000) Synaptic mechanisms and network dynamics underlying spatial working memory in a cortical network model. *Cereb Cortex* 10:910 –923.

# **Other Supporting Information Files**

[SI Appendix](http://www.pnas.org/cgi/data/0901894106/DCSupplemental/Appendix_PDF)